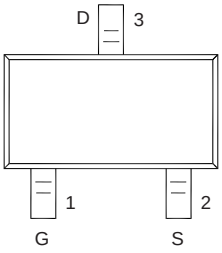
N-Channel 600 V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
600	80 at V_{GS} = 10 V	0.15

(SOT-23-3L)



Top View

FEATURES

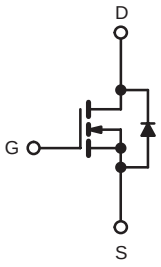
- DT-Trench II Power MOSFET
- 100% R_g and UIS Tested

Pb-free

RoHS COMPLIANT

APPLICATIONS

- High efficient switched mode power supplies
- TV Power
- Adapter/charger



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)[a]	T_A = 25 °C	I_D	0.15	A
	T_A = 70 °C		0.13	
Pulsed Drain Current		I_{DM}	0.6	
Avalanche Current		I_{AS}	0.12	
Peak diode recovery dv/dt		dv/dt	6	V/ns
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	2.5	W
	T_A = 70 °C		1.86	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient [a]	t ≤ 10 s	R_{thJA}	55	115	°C/W
	Steady State		38	85	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	12	28	

Notes:

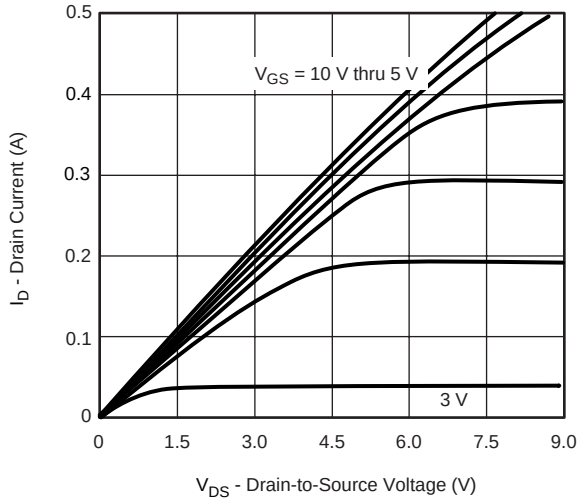
a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	600			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		0.6		V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V			1	µA
		V_{DS} = 600 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = - 10 V	19			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D =0.02 A		80	120	Ω
Forward Transconductance[a]	g_{fs}	V_{DS} = 40 V, I_D = 0.02 A		0.22		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} =300 V, V_{GS} = 0 V, f = 1 MHz		73		pF
Output Capacitance	C_{oss}			12		
Reverse Transfer Capacitance	C_{rss}			5		
Total Gate Charge	Q_g	V_{DS} = 300 V, V_{GS} = 10 V, I_D = 0.02 A		3.9		nC
Gate-Source Charge	Q_{gs}			0.28		
Gate-Drain Charge	Q_{gd}			2.6		
Gate Resistance	R_g	f = 1 MHz		6.5		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DS} = 300 V, R_L = 15 Ω $I_D \cong 0.02$ A, V_{GS} = 10 V, R_g = 1 Ω		7		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(off)}$			18		
Fall Time	t_f			52		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			0.15	A
Pulse Diode Forward Current[a]	I_{SM}				0.6	
Body Diode Voltage	V_{SD}	I_S = 0.15 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F =0.15 A, dI/dt = 100 A/µs, T_J = 25 °C		152		ns
Body Diode Reverse Recovery Charge	Q_{rr}			165		nC

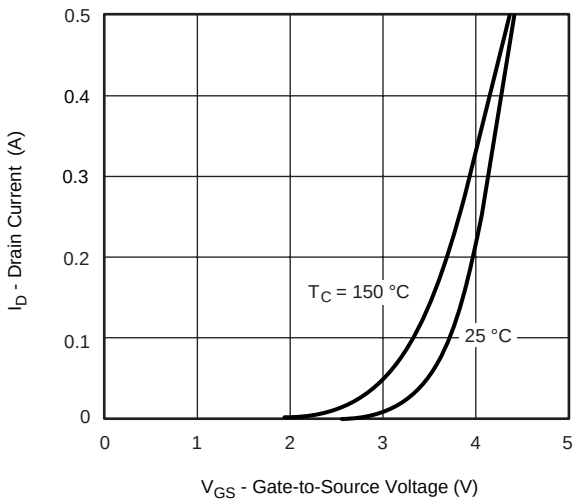
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

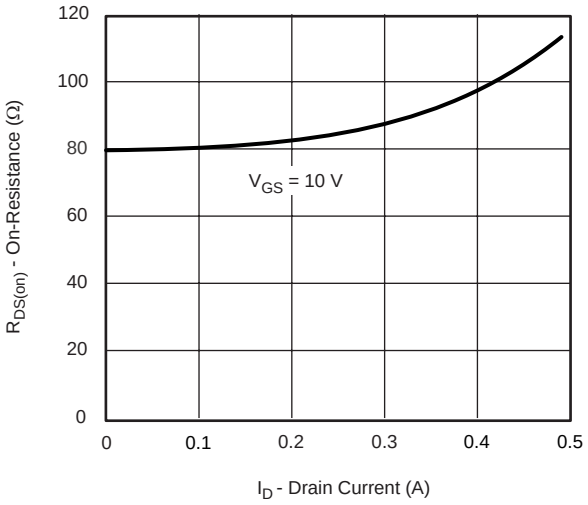
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



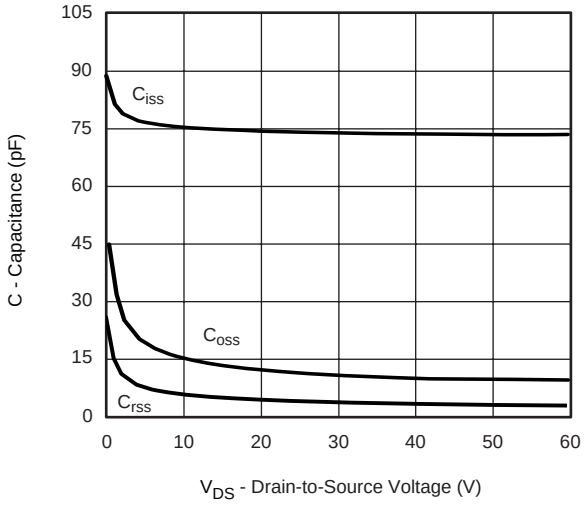
Output Characteristics



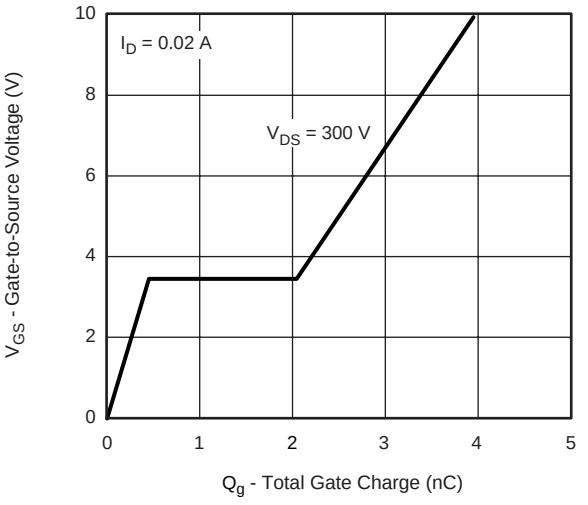
Transfer Characteristics



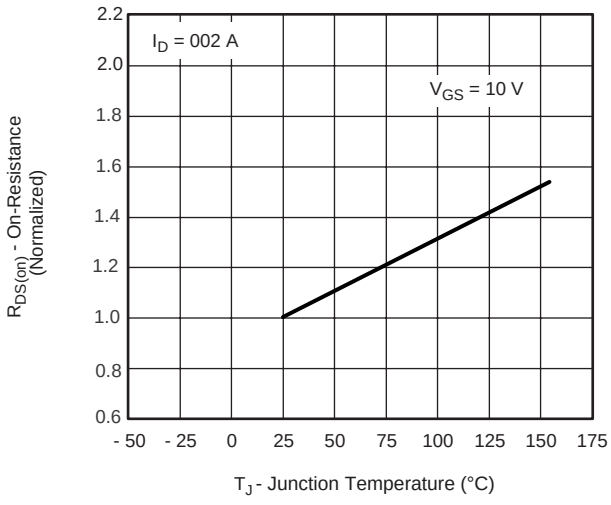
On-Resistance vs. Drain Current



Capacitance

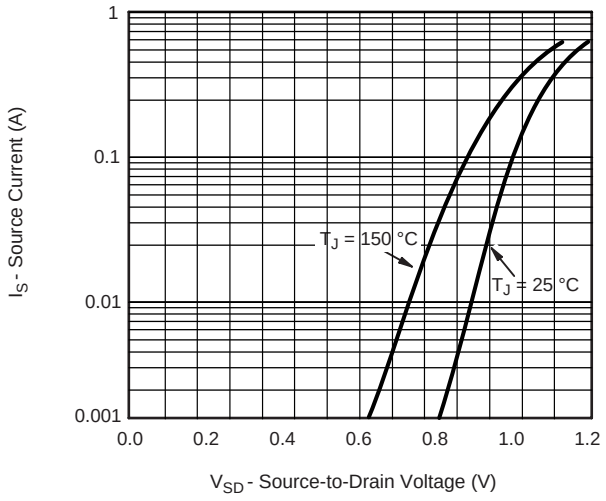


Gate Charge

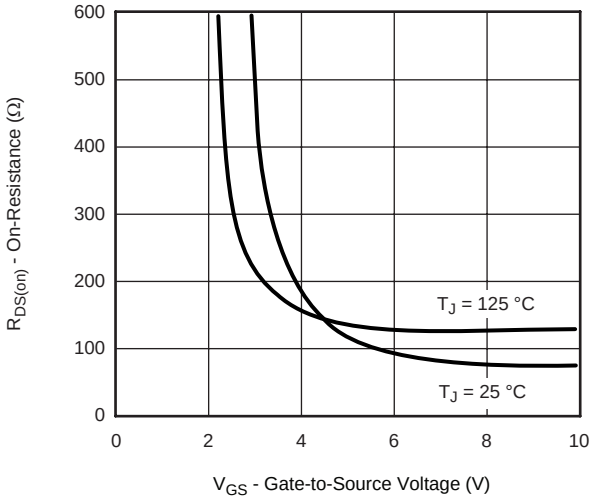


On-Resistance vs. Junction Temperature

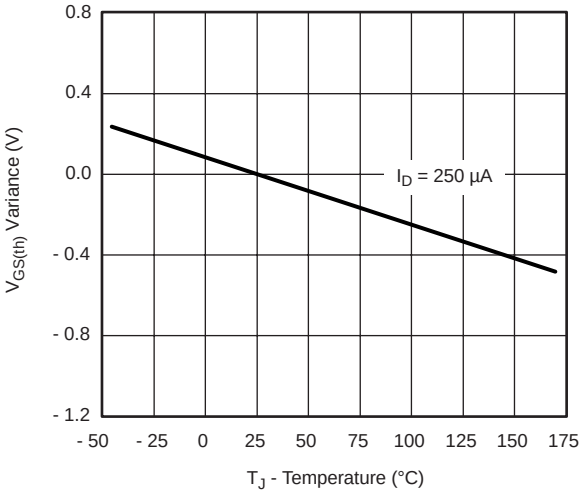
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



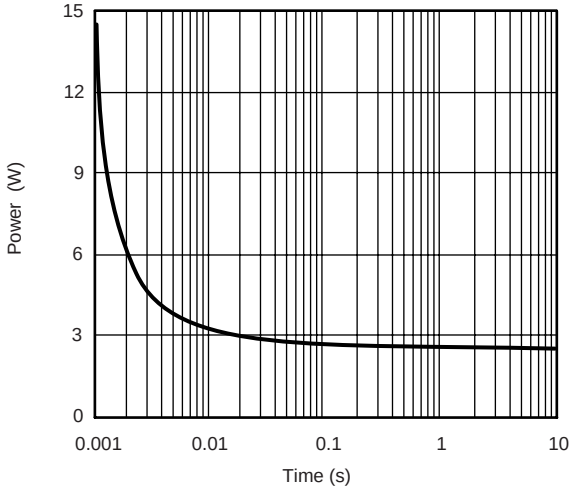
Source-Drain Diode Forward Voltage



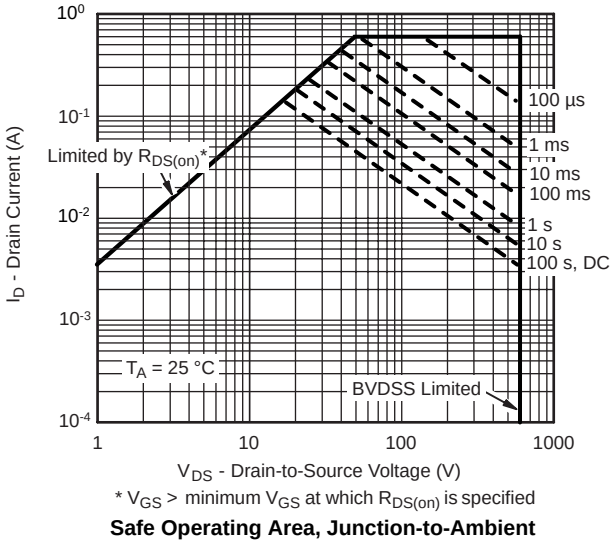
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

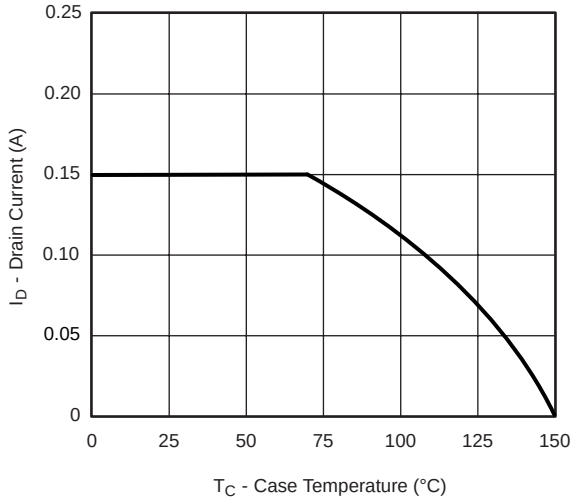


Single Pulse Power, Junction-to-Ambient



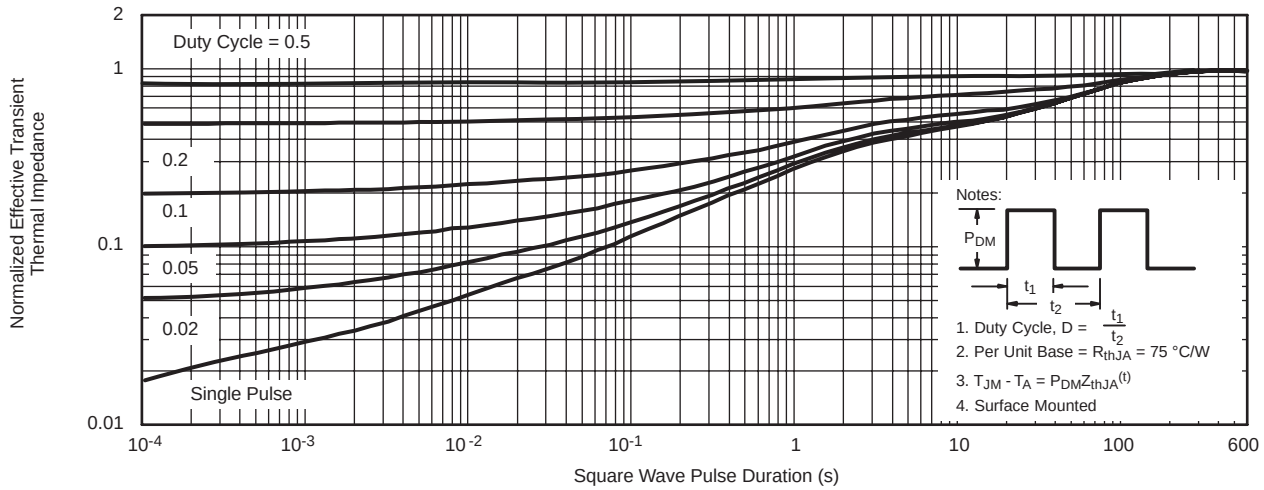
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient



Current Derating*

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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